

2SJ244

Silicon P Channel MOS FET

REJ03G0853-0200

(Previous: ADE-208-1187)

Rev.2.00 Sep 07, 2005

Description

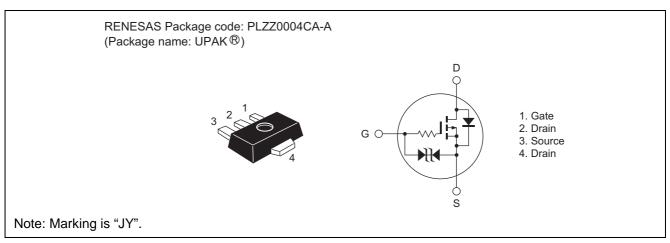
High speed power switching

Low voltage operation

Features

- Very Low on-resistance
- High speed switching
- Suitable for camera or VTR motor drive circuit, power switch, solenoid drive and etc.

Outline



*UPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit	
Drain to source voltage	V _{DSS}	-12	V	
Gate to source voltage	V_{GSS}	±7	V	
Drain current	I _D	±2	Α	
Drain peak current	I _{D (pulse)} Note 1	±4	A	
Channel dissipation	Pch Note 2	1	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW \leq 100 μ s, duty cycle \leq 10%

2. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

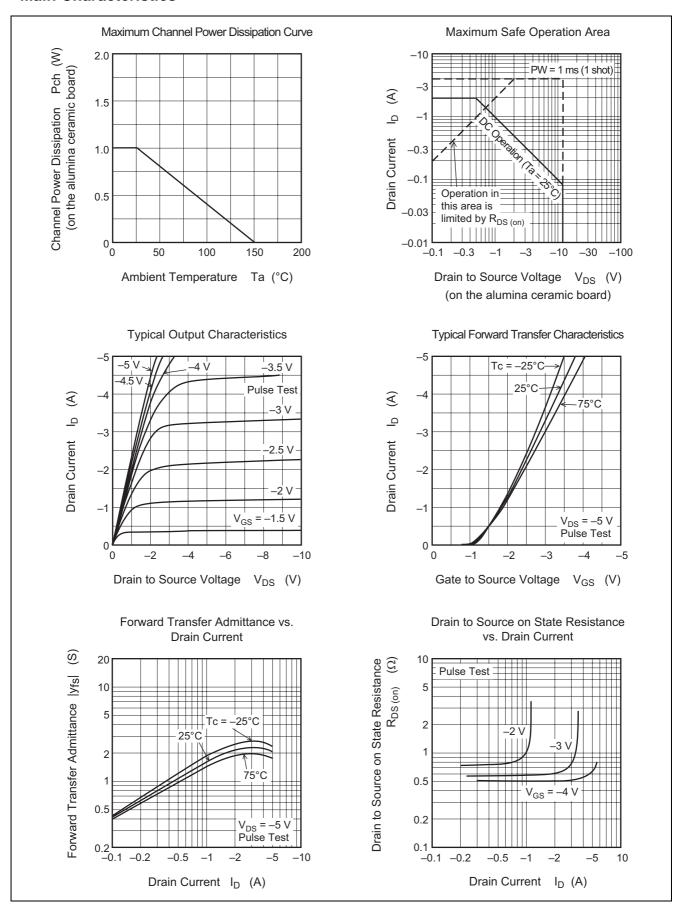
Electrical Characteristics

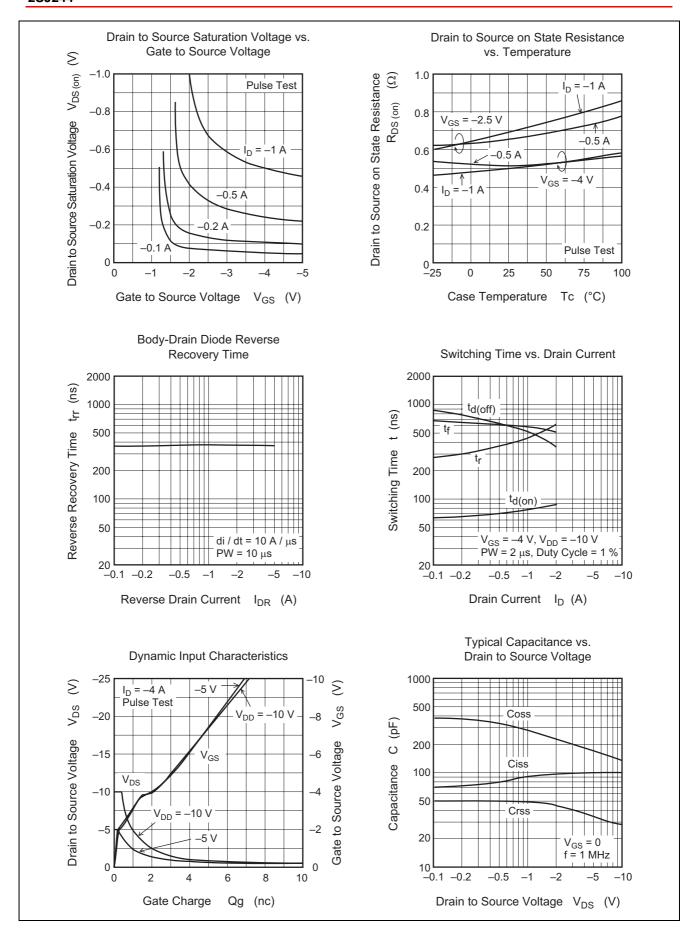
 $(Ta = 25^{\circ}C)$

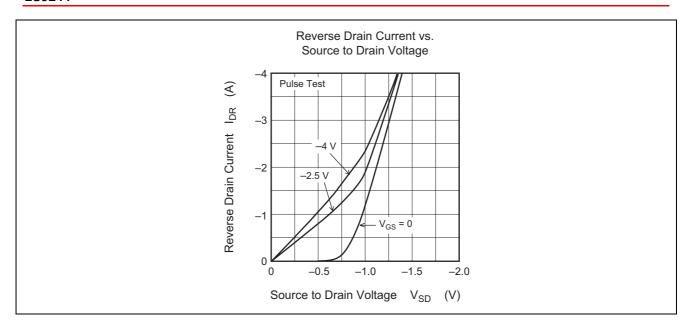
Symbol	Min	Тур	Max	Unit	Test Conditions
V _{(BR) DSS}	-12	_	_	V	$I_D = -1 \text{ mA}, V_{GS} = 0$
V _{(BR) GSS}	±7	_	_	V	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0$
I _{GSS}	_	_	±5	μΑ	$V_{GS} = \pm 6 \text{ V}, V_{DS} = 0$
I _{DSS}	_	_	-1	μΑ	$V_{DS} = -8 \text{ V}, V_{GS} = 0$
V _{GS (off)}	-0.4	_	-1.4	V	$I_D = -100 \ \mu A, \ V_{DS} = -5 \ V$
R _{DS (on) 1}	_	0.65	0.9	Ω	$I_D = -0.5 \text{ A}, V_{GS} = -2.5 \text{ V}^{\text{Note } 3}$
R _{DS (on) 2}	_	0.5	_	Ω	$I_D = -1 \text{ A}, V_{GS} = -4 \text{ V}^{\text{Note 3}}$
y _{fs}	_	1.8	_	S	$I_D = -1 A, V_{DS} = -5 V^{\text{Note 3}}$
Ciss	_	100	_	pF	$V_{DS} = -5 V$
Coss	_	168	_	pF	$V_{GS} = 0$
Crss	_	35	_	pF	f = 1 MHz
t _{d (on)}	_	365	_	ns	$I_D = -0.2 \text{ A}^{\text{Note 3}}$
t _{d (off)}	_	1450	_	ns	Vin = -4 V, $R_L = 51 \Omega$
V_{DF}	_	_	7	V	$I_F = 4 A^{\text{Note 3}}, V_{GS} = 0$
	V (BR) DSS V (BR) GSS IGSS IDSS VGS (off) RDS (on) 1 RDS (on) 2 Yfs Ciss Coss Crss td (on) td (off)	V (BR) DSS -12 V (BR) GSS ±7 I _{GSS} - I _{DSS} - V _{GS} (off) -0.4 R _{DS} (on) 1 - R _{DS} (on) 2 - Iyfs - Ciss - Coss - Crss - t _d (on) - t _d (off) -	V (BR) DSS -12 — V (BR) GSS ±7 — I _{GSS} — — I _{DSS} — — V _{GS} (off) — 0.65 R _{DS} (on) 1 — 0.5 Iyfs — 1.8 Ciss — 100 Coss — 168 Crss — 365 t _d (off) — 1450	V (BR) DSS -12 — — V (BR) GSS ±7 — — I _{GSS} — — ±5 I _{DSS} — — -1 V _{GS} (off) — 0.4 — — R _{DS} (on) 1 — 0.65 0.9 R _{DS} (on) 2 — 0.5 — Iyfsl — 1.8 — Ciss — 100 — Coss — 168 — Crss — 35 — t _d (on) — 365 — t _d (off) — 1450 —	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Note: 3. Pulse test

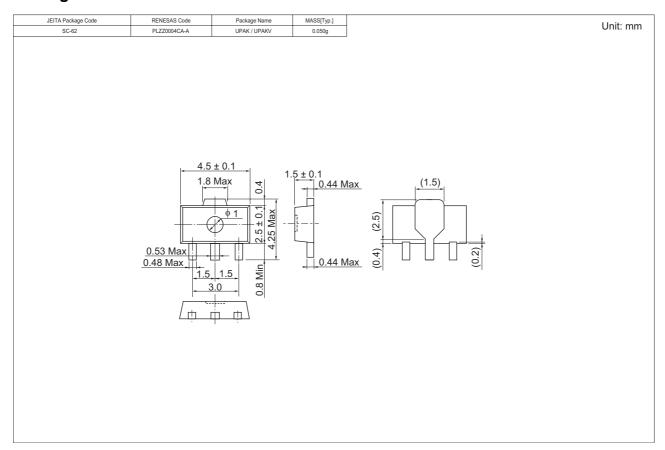
Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container			
2SJ244JYTL-E	1000 pcs	Taping			
2SJ244JYTR-E	1000 pcs	Taping			

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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